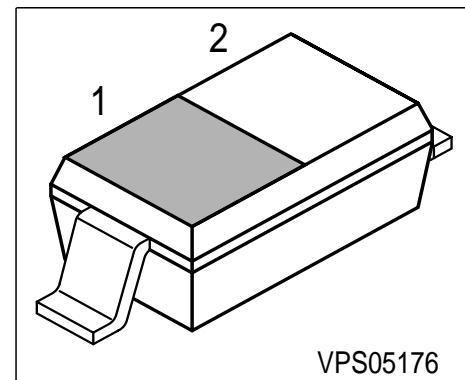


Silicon Schottky Diode

- High current rectifier Schottky diode with extreme low V_F drop
- For power supply
- For clamping and protection in low voltage applications
- For detection and step-up-conversion



ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration		Package
BAT60A	white/3	1 = C	2 = A	SOD323

Maximum Ratings

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	10	V
Forward current	I_F	3	A
Surge forward current ($t < 10\text{ms}$)	I_{FSM}	5	
Total power dissipation, $T_S = 28^\circ\text{C}$	P_{tot}	1350	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

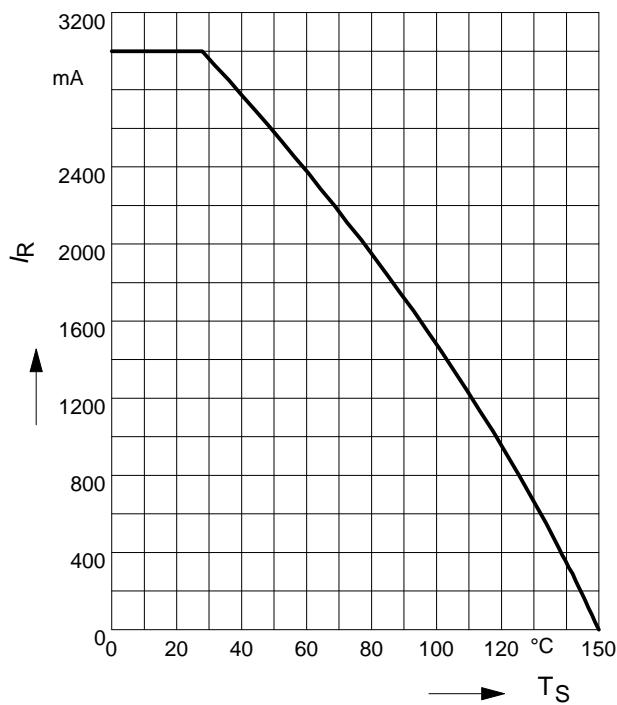
Junction - soldering point ¹⁾	R_{thJS}	≤ 90	K/W
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¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

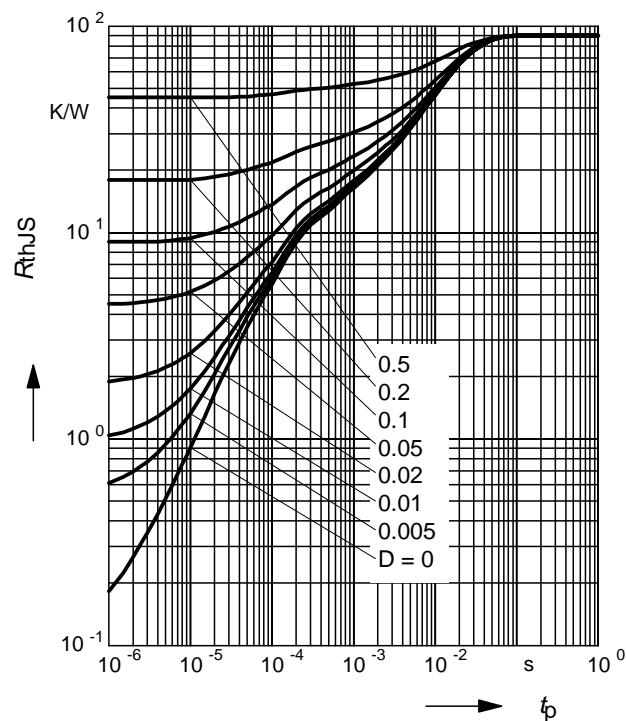
Electrical Characteristics at $T_A = 25 \text{ }^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Reverse current $V_R = 5 \text{ V}$	I_R	-	0.3	-	mA
$V_R = 8 \text{ V}$		-	0.6	2.6	
Reverse current $V_R = 8 \text{ V}, T_A = 80 \text{ }^\circ\text{C}$	I_R	-	18	-	
Forward voltage $I_F = 10 \text{ mA}$	V_F	0.1	0.12	0.15	V
$I_F = 100 \text{ mA}$		-	0.2	-	
$I_F = 1000 \text{ mA}$		-	0.3	-	
AC characteristics					
Diode capacitance $V_R = 5 \text{ V}, f = 1 \text{ MHz}$	C_T	-	20	-	pF

Forward current $I_F = f(T_S)$

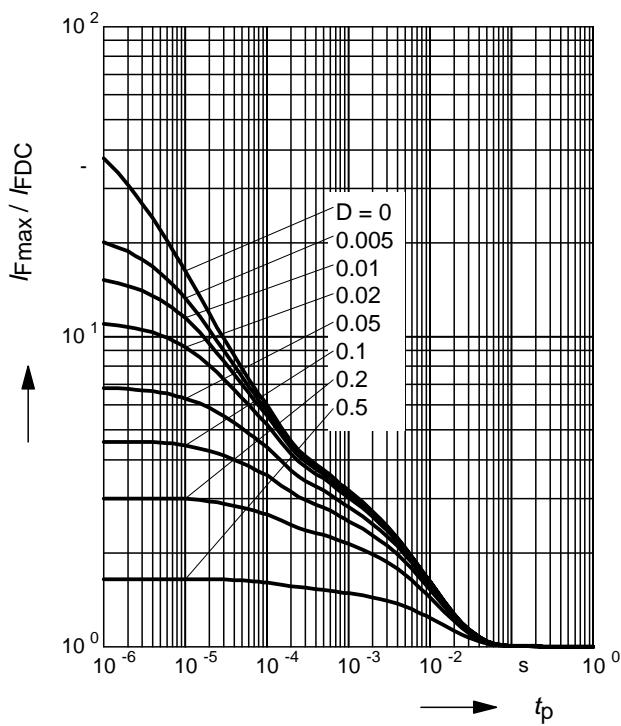


Permissible Pulse Load $R_{thJS} = f(t_p)$



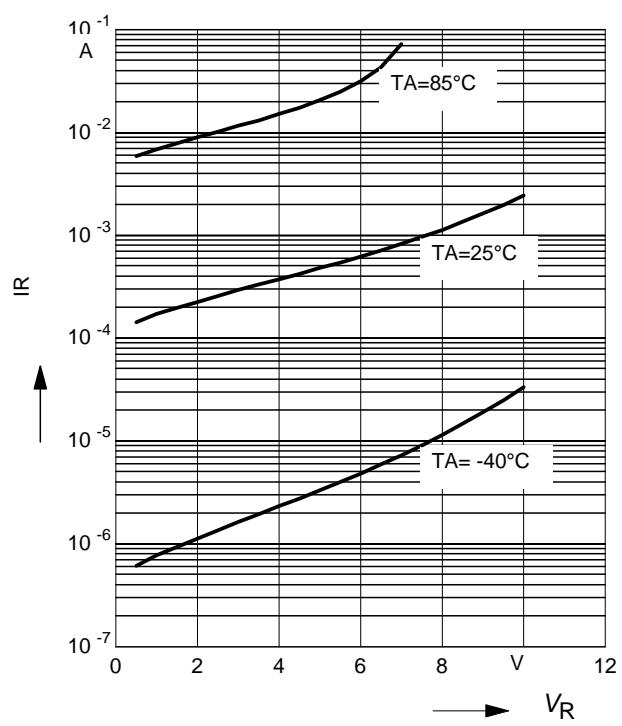
Permissible Pulse Load

$$I_{F\max} / I_{FDC} = f(t_p)$$



Reverse current $I_R = f(V_R)$

T_A = Parameter



Forward current $I_F = f(V_F)$

T_A = Parameter

